

P-Channel Enhancement Mode Field Effect Transistor

FEATURES

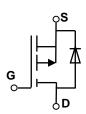
- Super high dense cell design for low RDS(ON)
- Rugged and reliable
- Simple drive requirement
- SOT-23 package

PRODUCT SUMMARY									
$V_{\rm DSS}$	ID	RDS(ON) (m Ω) Typ							
201/	2.04	130@ VGS=-10V							
-30V	-2.0A	150 @ VGS=-4.5V							



NOTE: The MT3405 is available in a lead-free package





ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	-30	V
Gate-Source Voltage	VGS	±20	V
Drain Current-Continuous ^a @Tj=125℃	ID	-2.6	A
- Pulse d^b	Ідм	-10	A
Drain-source Diode Forward Current ^a	Is	-1.25	A
Maximum Power Dissipation ^a	PD	1.25	W
Operating Junction and Storage Temperature Range	Tj,Tstg	-55 to 150	←

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to Ambient ^a	Rth JA	100	°C/W
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ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise noted)

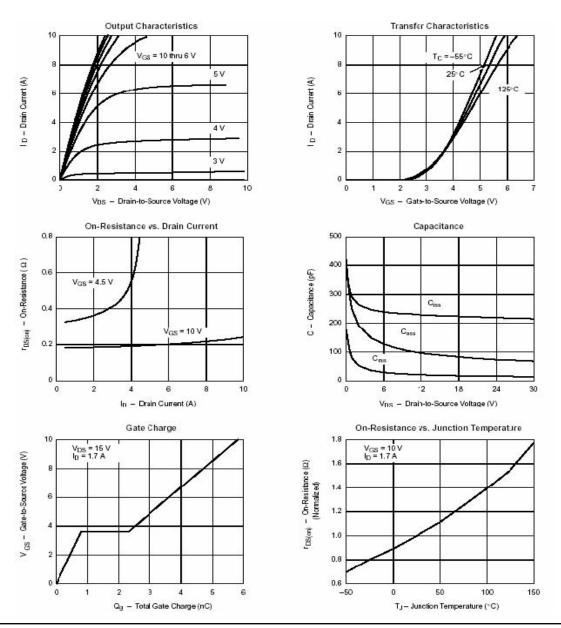
Parameter	Symbol	Condition	Min	Тур	Max	Unit			
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage	BVDSS	Vgs=0V,Id=-250µA	-30			V			
Zero Gate Voltage Drain Current	IDSS	Vds=-30V,Vgs=0V			1	μА			
Gate-Body Leakage	Igss	Vgs=±20V,Vds=0V			±100	nA			
ON CHARACTERITICS									
Gate Threshold Voltage	V _G s(th)	Vds=Vgs,Id=-250µA	-1.0		-3.0	V			
Dunin Course On State Presistance	Drawn	Vgs=-4.5V,ID=-4.0A		130	145				
Drain-Source On-State Resistance	RDS(ON)	Vgs=-2.5V,ID=-2.0A		150	168	mΩ			
Forward Transconductance	gFS	Vgs=-10V,ID=-2.6A		2.4		S			
DAYNAMIC CHARACTERISTICS			•						
Input Capacitance	Ciss			226		pF			
Output Capacitance	Coss	$V_{DS}=-15V, V_{GS}=-15V$ f=1.0MHz		87		pF			
Reverse Transfer Capacitance	Crss	1 1.01/1112		19		pF			
SWITCHING CHARACTERISISTICS									
Turn-On Delay Time	tD(ON)	Vdd=-15V		9.0		ns			
Rise Time	tr	ID=-1.0A,		9.0		ns			
Turn-Off Delay Time	td(OFF)	V _{GEN} =-10V R _L =150hm		18		ns			
Fall Time	tf	Rgen=60hm		6	20	ns			
Total Gate Charge	Q9			5.8	20	nC			
Gate-Source Charge	Qgs	Vds=-15V,Id=-1.7A Vgs=-10V		0.8	35	nC			
Gate-Drain Charge	Qgd	▼ 05—-10 ¥		1.5	20	nC			

ELECTRICAL CHARACTERICS (TA=25°C unless otherwise noted)

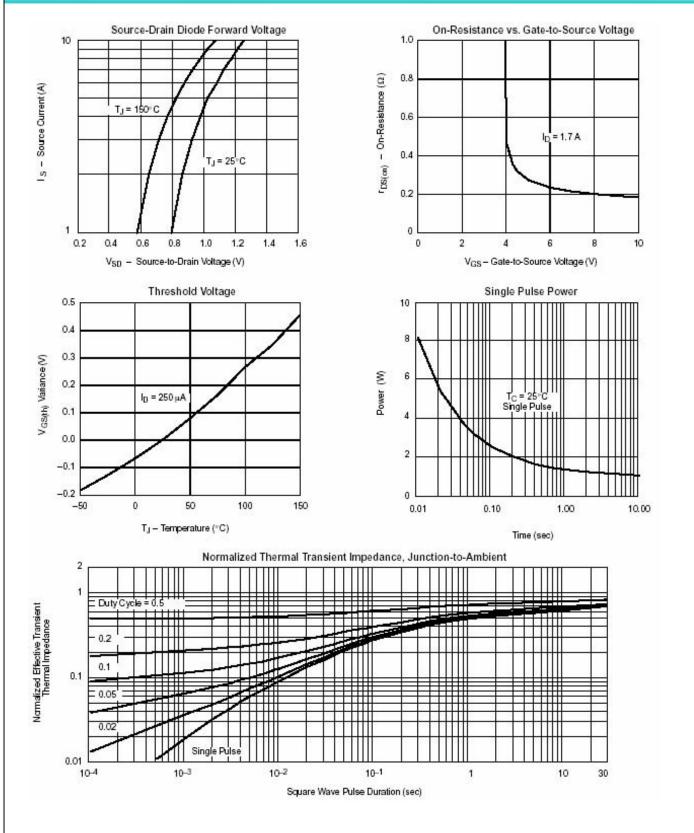
Parameter	Symbol	Condition	Min	Тур	Max	Unit				
DRAIN-SOURCE DIODE CHARACTERISTICS										
Diode Forward Voltage	Vsd	Vgs=0V,Is=-1.25A		-0.81	-1.2	V				

Notes

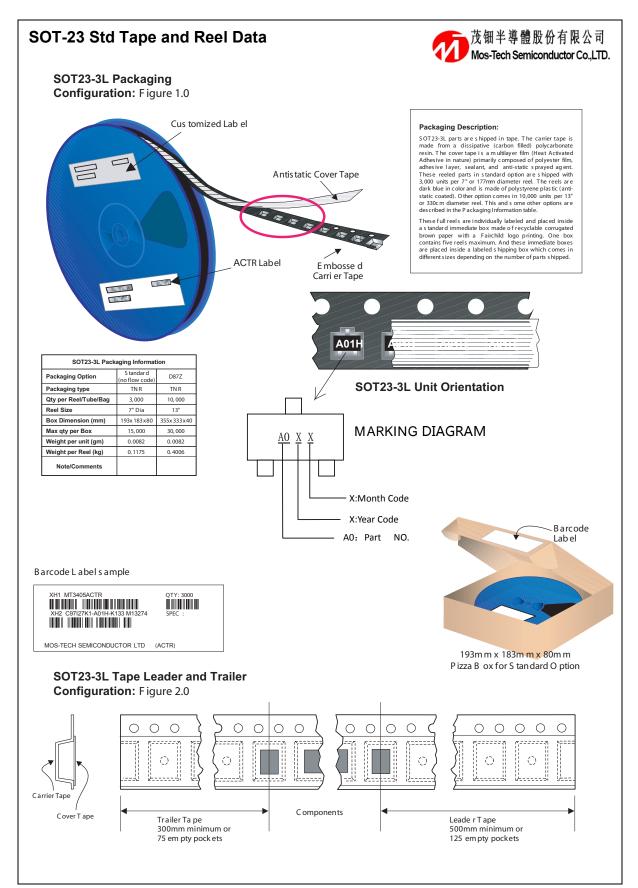
- a. Surface Mounted on FR4 Board, t ≤ 10sec
- b. Pulse Test: Pulse Width ≤ 300Us, Duty Cycle ≤ 2%
- c. Guaranteed by design, not subject to production testing.







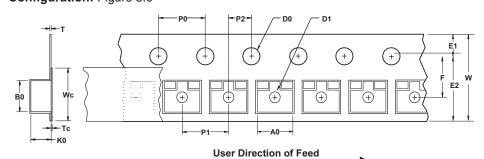
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SOT-23 Std Tape and Reel Data, continued



SOT23-3L Embossed Carrier Tape Configuration: Figure 3.0



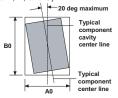
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

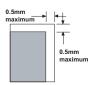


Sketch A (Side or Front Sectional View)

Component Rotation



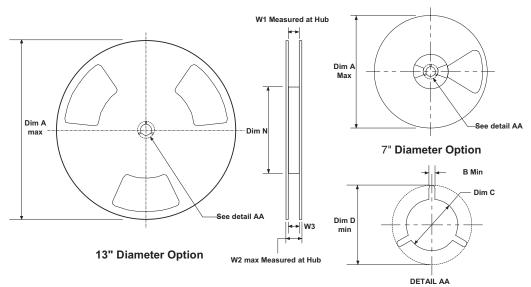
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

SOT23-3L Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters											
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)			
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9			
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10. 9			

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